



PATENT
Customer No. 22,852
Attorney Docket No. 03180.0289

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
)
Masayuki TANAKA, et al.) Group Art Unit: 2823
)
Serial No.: 09/973,744) Examiner: Fourson III, George R.
)
Filed: October 11, 2001)
)
For: METHOD OF MANUFACTURING)
SEMICONDUCTOR DEVICE AND)
THE SEMICONDUCTOR DEVICE)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

AMENDMENT

In reply to the Office Action of March 31, 2003, with a period for response extending through July 31, 2003, by the attached Petition for Extension of Time and requisite fee payment, please amend the application as follows. Applicants respectfully request the Examiner's reconsideration in view of the following remarks:

IN THE CLAIMS:

Please amend claims 1 and 8 – 10 as follows:

1. (Amended) A method of manufacturing a semiconductor device, comprising:

forming an insulating film on a silicide layer formed at the surface of a silicon semiconductor substrate;

etching the insulating film to form a contact hole in which the silicide layer is exposed;

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